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2015年3月

FCPF190N65FL1

N-沟道 SuperFET® II FRFET® MOSFET

650 V, 20.6 A, 190 mΩ

特性

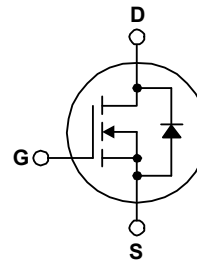
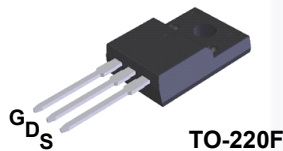
- 700 V @ $T_J = 150\text{ }^\circ\text{C}$
- $R_{DS(on)} = 168\text{ m}\Omega$ (典型值)
- 超低栅极电荷 (典型值 $Q_g = 60\text{ nC}$)
- 低有效输出电容 (典型值 $C_{oss(eff.)} = 304\text{ pF}$)
- 100% 经过雪崩测试
- 符合 RoHS 标准

应用

- LCD / LED / PDP TV
- 通信 / 服务器电源
- 太阳能变频器
- AC-DC 电源

描述

SuperFET® II MOSFET 是飞兆利用电荷平衡技术实现出色的低导通电阻和更低栅极电荷性能的全新高压超级结 (SJ) MOSFET 系列产品。这项技术专用于最小化导通损耗并提供卓越的开关性能、 dv/dt 额定值和更高雪崩能量。因此, SuperFET MOSFET 非常适合开关电源应用, 如功率因数校正 (PFC)、服务器 / 电源、平板电视电源、ATX 电源及工业电源应用。SuperFET II FRFET® MOSFET 优化体二极管的反向恢复性能可去除额外元件, 提高系统可靠性。



最大绝对额定值 $T_C = 25\text{ }^\circ\text{C}$ 除非另有说明。

符号	参数	FCPF190N65FL1	单位
V_{DSS}	漏极-源极电压	650	V
V_{GSS}	栅极-源极电压	- DC	± 20
		- AC ($f > 1\text{ Hz}$)	± 30
I_D	漏极电流	- 连续 ($T_C = 25\text{ }^\circ\text{C}$)	20.6
		- 连续 ($T_C = 100\text{ }^\circ\text{C}$)	13.1
I_{DM}	漏极电流	- 脉冲 (注 1)	61.8
E_{AS}	单脉冲雪崩能量	(注 2)	400
I_{AR}	雪崩电流	(注 1)	4
E_{AR}	重复雪崩能量	(注 1)	2.1
dv/dt	MOSFET dv/dt		100
	二极管恢复 dv/dt 峰值	(注 3)	50
P_D	功耗	($T_C = 25\text{ }^\circ\text{C}$)	39
		- 高于 $25\text{ }^\circ\text{C}$ 的功耗系数	0.31
T_J, T_{STG}	工作和存储温度范围		-55 至 +150
T_L	用于焊接的最大引脚温度, 距离外壳 1/8", 持续 5 秒		300

热性能

符号	参数	FCPF190N65FL1	单位
$R_{\theta JC}$	结至外壳热阻最大值	3.2	$^\circ\text{C/W}$
$R_{\theta JA}$	结至环境热阻最大值	62.5	

FCPF190N65FL1 — N-沟道 SuperFET® II FRFET® MOSFET

封装标识与订购信息

器件编号	顶标	封装	包装方法	卷尺寸	带宽	数量
FCPF190N65FL1	FCPF190N65F	TO-220F	塑料管	不适用	不适用	50 个

电气特性 $T_C = 25^\circ\text{C}$ 除非另有说明。

符号	参数	测试条件	最小值	典型值	最大值	单位
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关断特性

BV_{DSS}	漏极-源极击穿电压	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	650	-	-	V
		$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 150^\circ\text{C}$	700	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	击穿电压温度系数	$I_D = 1\text{ mA}$, 参考 25°C 数值	-	0.71	-	V/ $^\circ\text{C}$
I_{DSS}	零栅极电压漏极电流	$V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$	-	-	10	μA
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_C = 125^\circ\text{C}$	-	60	-	
I_{GSS}	栅极-体漏电流	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	± 100	μA

导通特性

$V_{GS(th)}$	栅极阈值电压	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	3	-	5	V
$R_{DS(on)}$	漏极至源极静态导通电阻	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$	-	168	190	m Ω
g_{FS}	正向跨导	$V_{DS} = 20\text{ V}, I_D = 10\text{ A}$	-	18	-	S

动态特性

C_{iss}	输入电容	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	2350	3055	pF
C_{oss}	输出电容		-	77	100	pF
C_{rss}	反向传输电容		-	0.68	-	pF
C_{oss}	输出电容	$V_{DS} = 380\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	44	-	pF
$C_{oss(eff.)}$	有效输出电容	$V_{DS} = 0\text{ V}$ 至 $400\text{ V}, V_{GS} = 0\text{ V}$	-	304	-	pF
$Q_g(\text{tot})$	10 V 的栅极电荷总量	$V_{DS} = 380\text{ V}, I_D = 10\text{ A}, V_{GS} = 10\text{ V}$ (注 4)	-	60	78	nC
Q_{gs}	栅极-源极栅极电荷		-	12	-	nC
Q_{gd}	栅极-漏极“米勒”电荷		-	25	-	nC
ESR	等效串联电阻	$f = 1\text{ MHz}$	-	0.6	-	Ω

开关特性

$t_{d(on)}$	导通延迟时间	$V_{DD} = 380\text{ V}, I_D = 10\text{ A}, V_{GS} = 10\text{ V}, R_g = 4.7\ \Omega$ (注 4)	-	25	60	ns
t_r	导通上升时间		-	11	32	ns
$t_{d(off)}$	关断延迟时间		-	62	134	ns
t_f	关断下降时间		-	4.2	18	ns

漏极-源极二极管特性

I_S	漏极-源极二极管最大正向连续电流	-	-	20.6	A	
I_{SM}	漏极-源极二极管最大正向脉冲电流	-	-	61.8	A	
V_{SD}	漏极-源极二极管正向电压	$V_{GS} = 0\text{ V}, I_{SD} = 10\text{ A}$	-	-	1.2	V
t_{rr}	反向恢复时间	$V_{GS} = 0\text{ V}, I_{SD} = 10\text{ A}$	-	105	-	ns
Q_{rr}	反向恢复电荷	$di/dt = 100\text{ A}/\mu\text{s}$	-	515	-	nC

注:

- 重复额定值: 脉冲宽度受限于最大结温。
- $I_{AS} = 4\text{ A}$, $R_G = 25\ \Omega$, 开始于 $T_J = 25^\circ\text{C}$ 。
- $I_{SD} \leq 10\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq 380\text{ V}$, 开始于 $T_J = 25^\circ\text{C}$ 。
- 典型特性本质上独立于工作温度。

典型性能特征

图 1. 导通区域特性

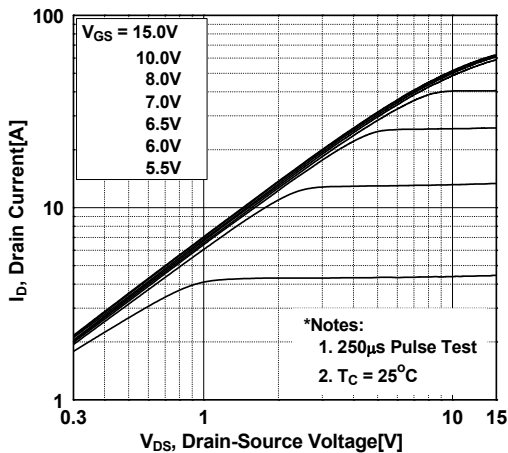


图 2. 传输特性

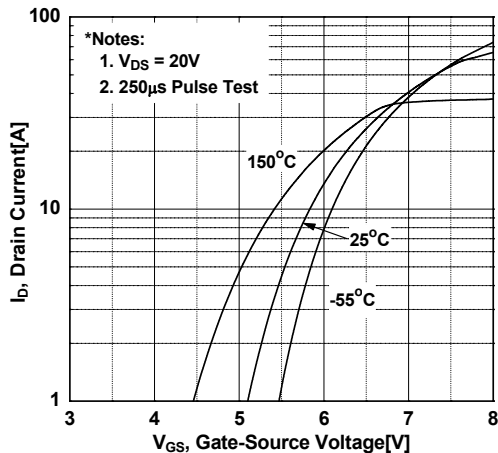


图 3. 导通电阻变化与漏极电流和栅极电压的关系

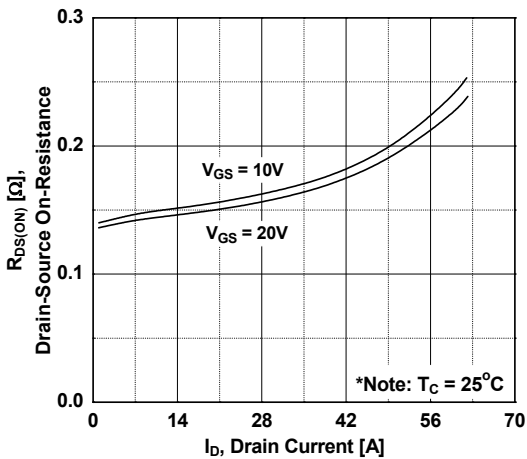


图 4. 体二极管正向电压变化与源极电流和温度的关系

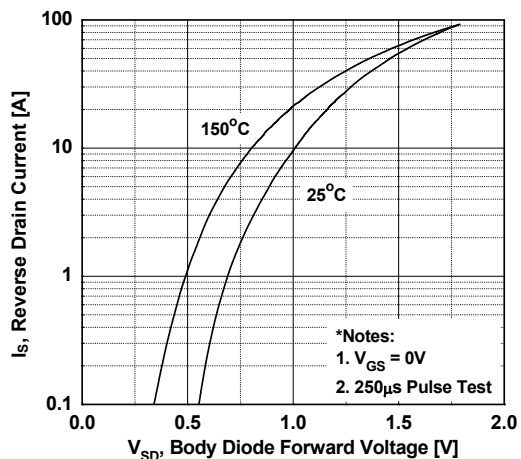


图 5. 电容特性

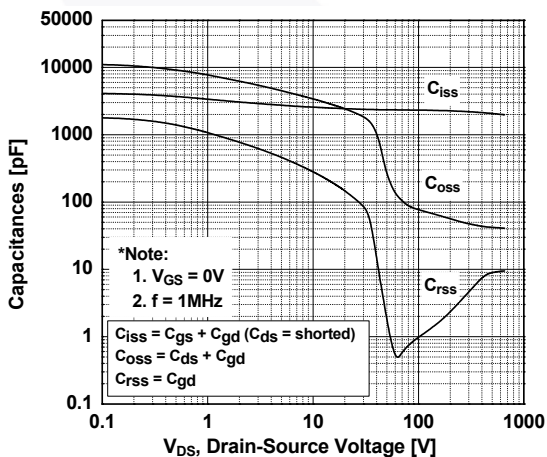
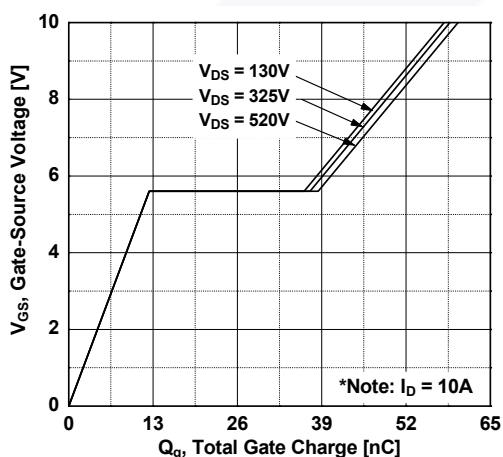


图 6. 栅极电荷特性



典型性能特征 (接上页)

图 7. 击穿电压变化与温度的关系

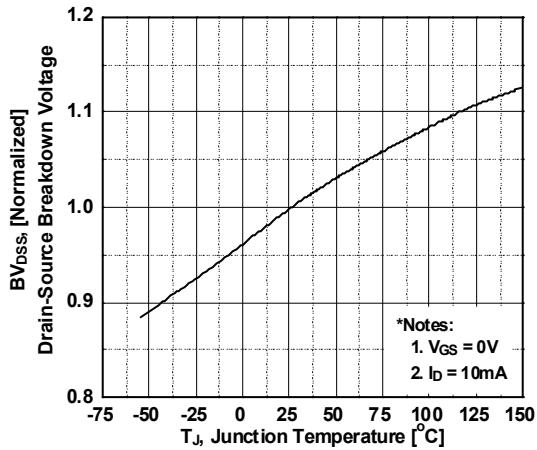


图 8. 导通电阻变化与温度的关系

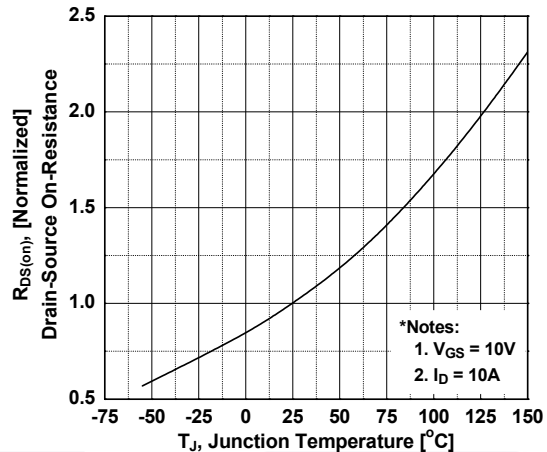


图 9. 最大安全工作区

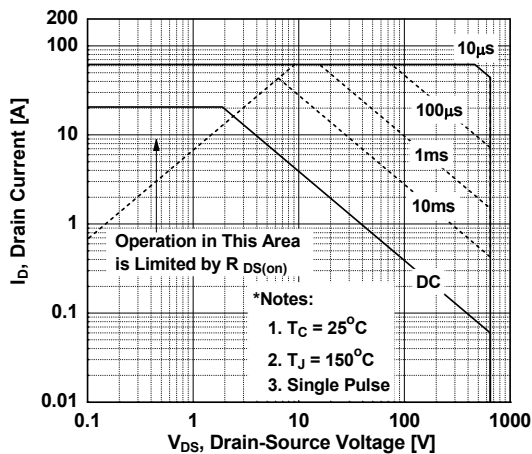


图 10. 最大漏极电流与壳温的关系

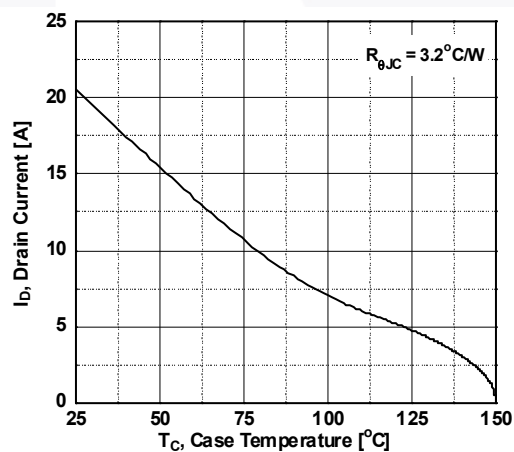
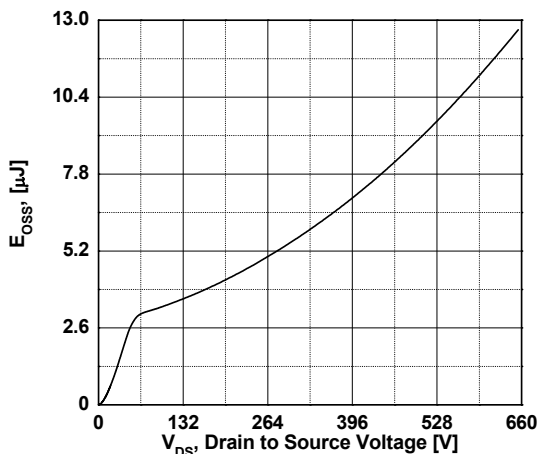
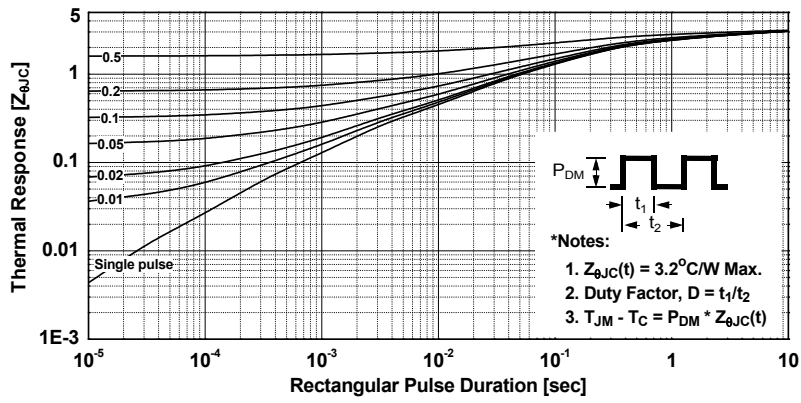


图 11. E_oss 与漏源极电压的关系



典型性能特征 (接上页)

图 12. 瞬态热响应曲线



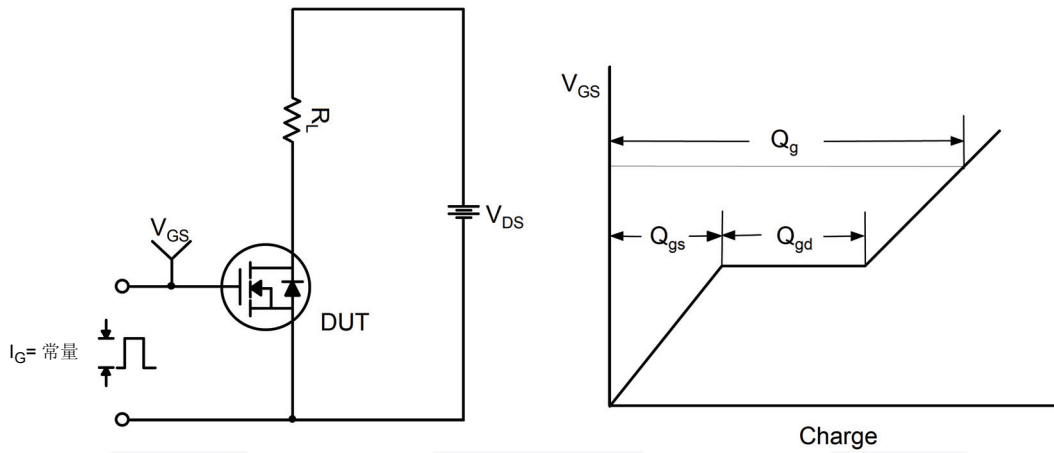


图 13. 栅极电荷测试电路与波形

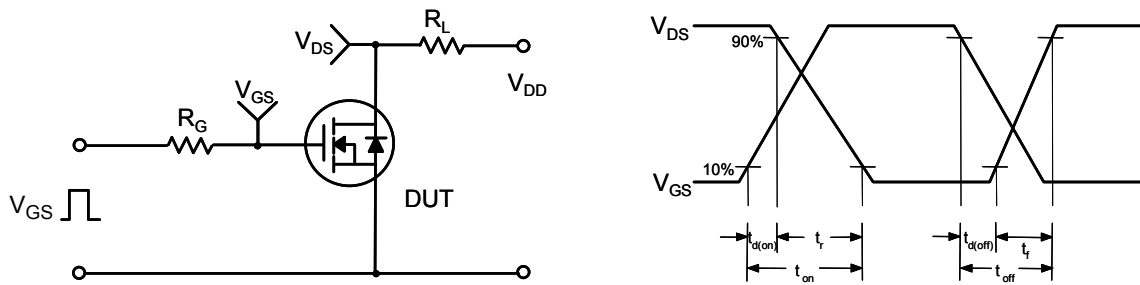


图 14. 阻性开关测试电路与波形

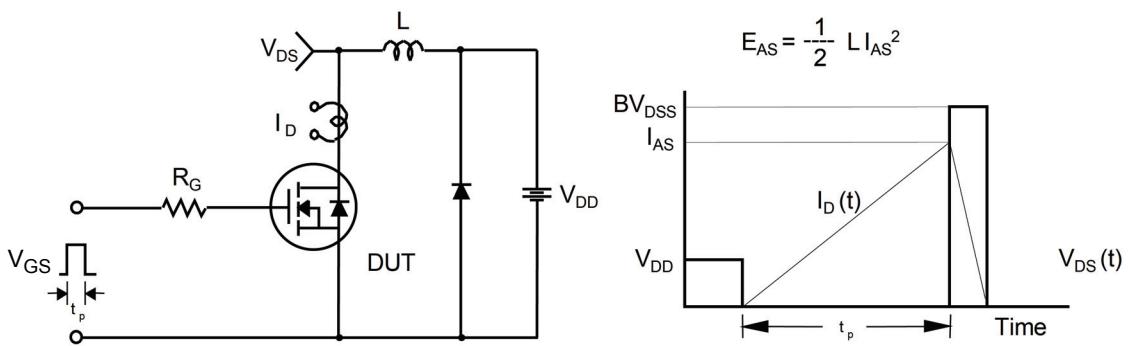


图 15. 非箝位电感开关测试电路与波形

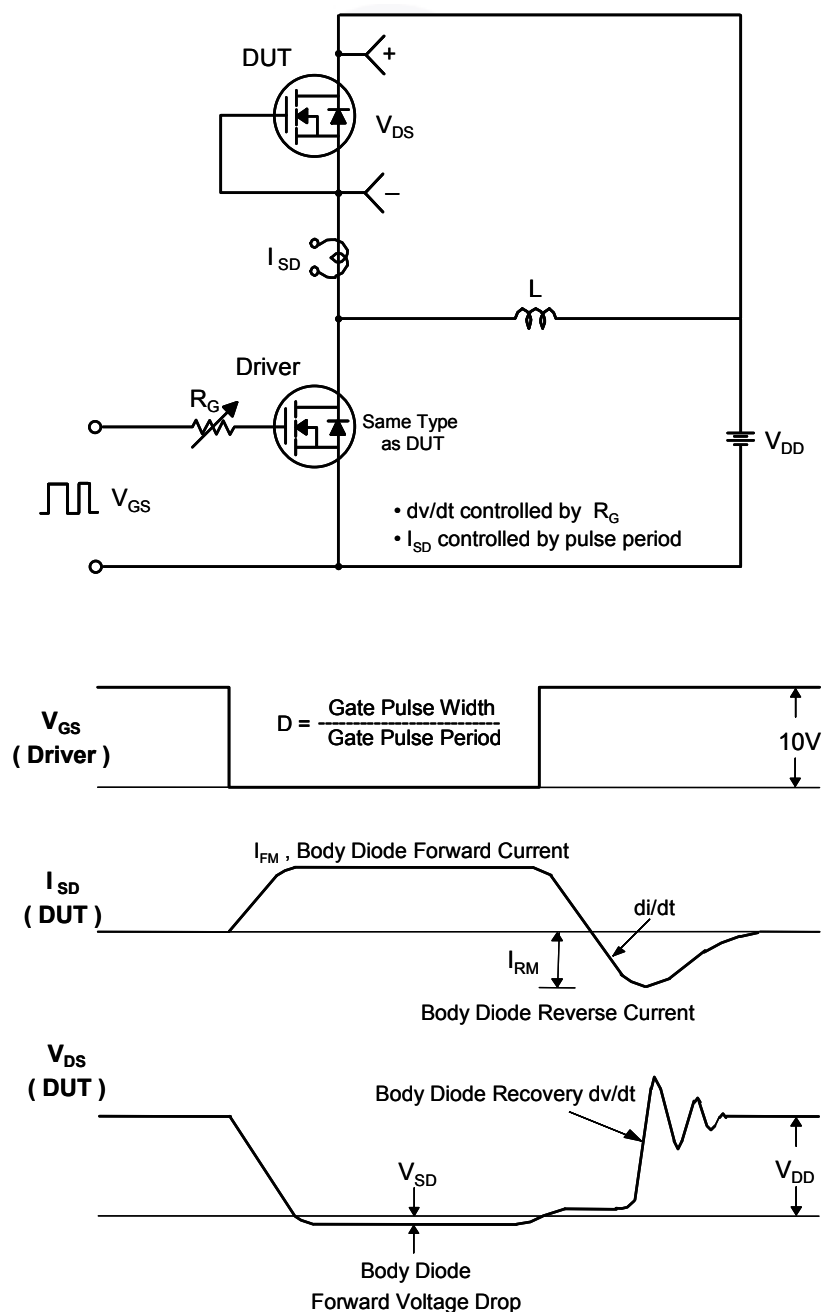


图 16. 二极管恢复 dv/dt 峰值测试电路与波形

机械尺寸

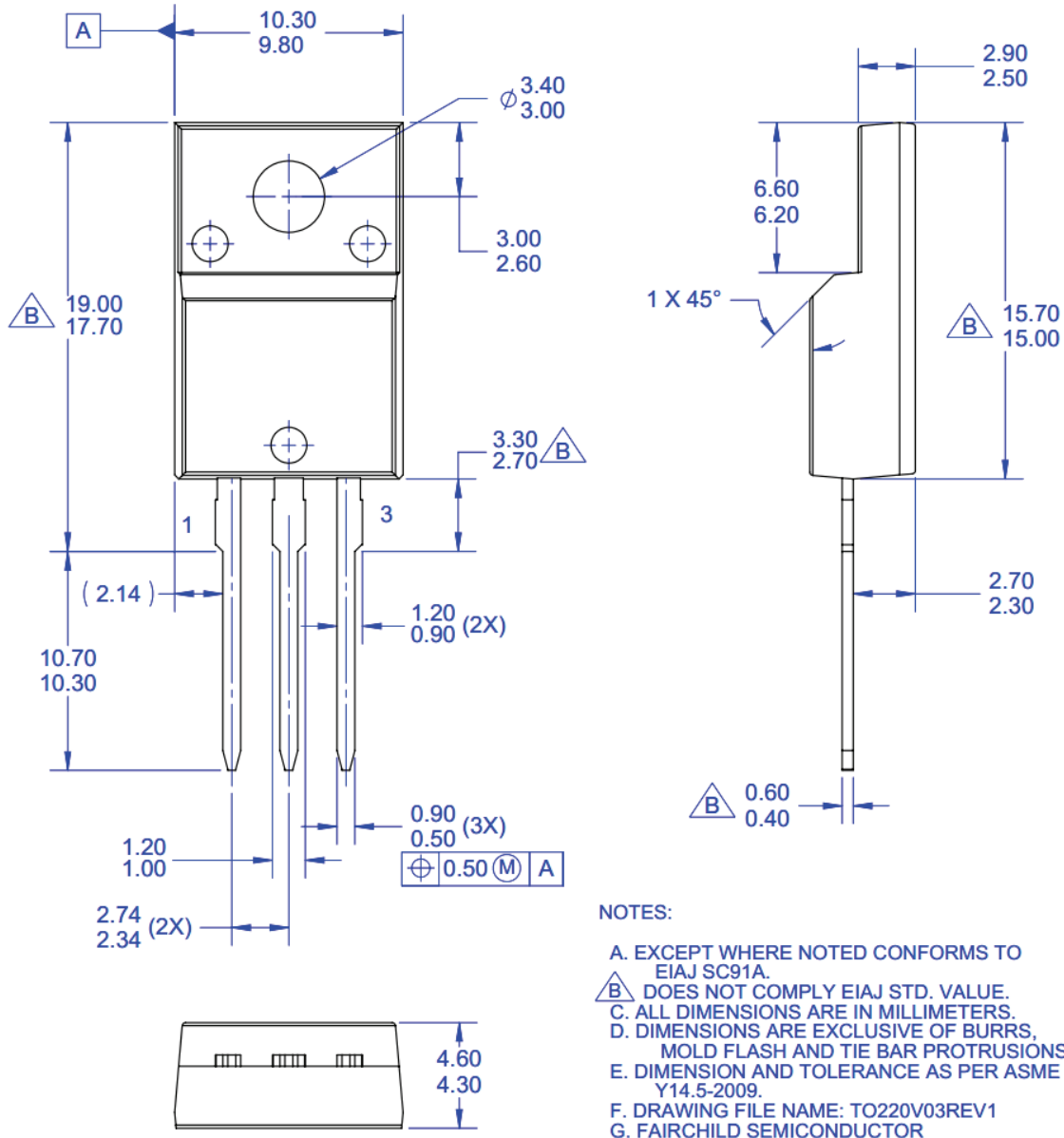


图 17. TO220 模塑 3 引脚 Full Pack, EIAJ SC91, Takcheong

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